	Time S	Stamp	Comments	Error	Definition	Errors
31	2002/12 17:08	2/12				0
32	2002/12 17:17	2/12				0
33	2002/12 17:21	2/12				0
34	2002/12 17:24	2/12				0
35	2002/12 17:25	/12				0
36	2002/12 12:39	/13				0
37	2002/12 11:28	/13				0
38	2002/12 12:41	/13				0
39	2002/12 12:41	/13				0
40	2002/12	/13				0
1/1/1/1	2002/12 12:41	/13				0

	Туре	Hits	Search Text	DBs
1	BRS	2	WO-9639713-\$.did.	USPAT; US-PGPUB; EPO; JPO;
2	BRS	2	JP-06302813-\$.did.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;
			,	DERWENT; IBM_TDB USPAT; US-PGPUB;
3	BRS	2	6417546.pn.	EPO; JPO; DERWENT; IBM_TDB
4	BRS	2	6093661.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	3	6093661.URPN.	USPAT
6	BRS	0	6417546.URPN.	USPAT
7	BRS	16	("4651406" "5254489" "5464792" "5502009" "5596218" "5620908" "5674788" "5716864" "5960302" "5972783" "5994749" "6136654" "6153538" "6165846" "6200834" "6225151").PN.	USPAT
8	BRS	5	("5254489" "5464792" "5620908" "5716864" "5972783").PN.	USPAT
9	BRS	388	438/199.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
10	BRS	487	438/207.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	104	438/288.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	444	438/296.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
13	BRS	78	438/513.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
14	BRS		438/769.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
15	BRS	1	(cmos near3 transistor) and (substrate same (silicon adj dioxide) same plasma same nitrogen same (silicon adj nitride))	
16	BRS	137	(transistor) and (substrate same (silicon adj dioxide) same nitrogen same (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	min at	Τ= .		T
	Time Stamp	Comments	Error Definition	Errors
1	2002/09/17 16:33			0
2	2002/09/17 16:33			0
3	2002/11/05 15:24			0
4	2002/11/05 15:26			0
5	2002/11/05 15:27			0
6	2002/11/05 15:27			0
7	2002/11/05 15:28			0
8	2002/11/05 15:29			0
9	2002/11/05 17:09			0
10	2002/11/05 17:09			0
11	2002/11/05 17:09			0
12	2002/11/05 17:09			0
13	2002/11/05 17:10			0
14	2002/11/05 17:10			0
15	2002/11/05 17:15			0
16	2002/11/05 17:20			0

	Туре	Hits	Search Text	DBs
17	BRS	1	(transistor) and (substrate same (gate adj oxide with silicon adj dioxide) same nitrogen same (silicon adj nitride))	EPO; JPO; DERWENT; IBM_TDB
18	BRS	73	(transistor) and (substrate same (gate adj oxide) same nitrogen same (silicon adj nitride))	
19	BRS	155	438/775.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	22	438/775.ccls. and activat\$3 and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	13	438/775.ccls. and (plasma with power) and anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	20	438/775.ccls. and (plasma with power)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	1	438/775.ccls. and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3) same rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	1	438/775.ccls. and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3) same ramp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	2	438/775.ccls. and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3 or RTP) same rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	26	time same (rapid adj thermal adj process\$3 or RTP) same rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	8	time same (rapid adj thermal adj process\$3 or RTP) same rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	BRS	6	time same (rapid adj thermal adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	BRS	2	(surface near3 temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30	BRS	7	(surface near3 temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamr	Comments	Error Definition	Errors
17	2002/12/12			0
18	2002/11/05			0
19	2002/11/05 17:43			0
20	2002/11/05 18:16			0
21	2002/11/05 17:55			0
22	2002/11/05 18:04			0
23	2002/11/05 18:06			0
24	2002/11/05 18:06			0
25	2002/11/05 18:10			0
26	2002/11/05 18:11			0
27	2002/11/05 18:12			0
28	2002/11/05 18:13			0
29	2002/11/05 18:18			0
	2002/11/05 18:17			0

	Туре	Hits	Search Text	DBs
31	BRS	141	(transistor) and (substrate same (silicon adj dioxide) same nitrogen same (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32	BRS	6	(transistor) and (substrate same (silicon adj dioxide) same nitrogen same (silicon adj nitride)) and ((nitride or nitrogen) with atom\$2 with (percent or "%"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
33	BRS	3	(transistor) and (substrate same (gate adj oxide) same nitrogen same (silicon adj nitride)) and ((nitride or nitrogen) with atom\$2 with (percent or "%"))	USPAT; US-PGPUB; EPO; JPO;
34	BRS	44	(transistor) and (substrate same nitrogen same (silicon adj nitride)) and ((nitride or nitrogen) with atom\$2 with (percent or "%"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	BRS	42	(transistor) and (substrate same nitrogen with (implant\$5 or diffus\$3)) and ((nitride or nitrogen) with atom\$2 with (percent or "%"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36	BRS	1268	(transistor) and (substrate same nitrogen with (implant\$5 or diffus\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
37	BRS	7	("5254489" "5716863" "5763922" "5989962" "6048769" "6093661" "6171911").PN.	USPAT
38	BRS	71	(transistor) and (substrate same nitrogen with activat\$3 same temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
39	BRS	168	activat\$3 same temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
40	BRS	68	accivacas with temperature;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
41	BRS	17	nitrogen with activat\$3 with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB